

NDF02N60Z, NDP02N60Z, NDD02N60Z

N-Channel Power MOSFET 600 V, 4.0 Ω

Features

- Low ON Resistance
- Low Gate Charge
- 100% Avalanche Tested
- These Devices are Pb-Free and are RoHS Compliant

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	NDF	NDP	NDD	Unit
Drain-to-Source Voltage	V_{DS}	600			V
Continuous Drain Current $R_{\theta JC}$	I_D	2.4 (Note 1)	2.4	2.2	A
Continuous Drain Current $R_{\theta JC}$ $T_A = 100^\circ\text{C}$	I_D	1.6 (Note 1)	1.6	1.4	A
Pulsed Drain Current, V_{GS} @ 10 V	I_{DM}	10 (Note 1)	10	9	A
Power Dissipation $R_{\theta JC}$	P_D	24	72	57	W
Gate-to-Source Voltage	V_{GS}	30			V
Single Pulse Avalanche Energy, $I_D = 2.4$ A	E_{AS}	120			mJ
ESD (HBM) (JESD 22-A114)	V_{esd}	2500			V
RMS Isolation Voltage ($t = 0.3$ sec., R.H. $\leq 30\%$, $T_A = 25^\circ\text{C}$) (Figure 17)	V_{ISO}	4500			V
Peak Diode Recovery	dv/dt	4.5 (Note 2)			V/ns
Continuous Source Current (Body Diode)	I_S	2.4			A
Maximum Temperature for Soldering Leads	T_L	260			$^\circ\text{C}$
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150			$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

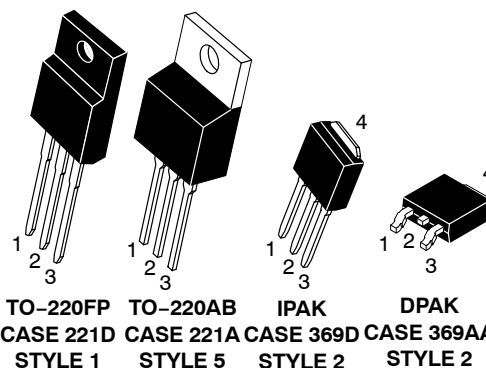
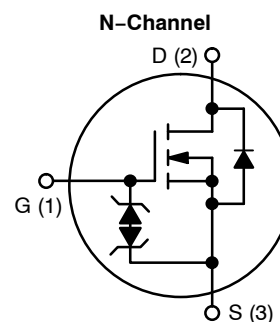
1. Limited by maximum junction temperature
2. $I_{SD} = 2.4$ A, $dv/dt \leq 100$ A/ μs , $V_{DD} \leq BV_{DSS}$, $T_J = +150^\circ\text{C}$



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<http://onsemi.com>

V_{DSS}	$R_{DS(on)}$ (TYP) @ 1 A
600 V	4.0 Ω



MARKING AND ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

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THERMAL RESISTANCE

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain)	$R_{\theta JC}$	1.7 5.2 2.2	°C/W
Junction-to-Ambient Steady State	$R_{\theta JA}$	51 51 41 80	

3. Insertion mounted

4. Surface mounted on FR4 board using 1" sq. pad size, (Cu area = 1.127 in sq [2 oz] including traces).

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Test Conditions	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	BV_{DSS}	600			V
Breakdown Voltage Temperature Coefficient	Reference to 25°C , $I_D = 1\text{ mA}$	$\Delta BV_{DSS} / \Delta T_J$		0.6		V/°C
Drain-to-Source Leakage Current	$V_{DS} = 600\text{ V}, V_{GS} = 0\text{ V}$	I_{DSS}	25°C		1	μA
			150°C		50	
Gate-to-Source Forward Leakage	$V_{GS} = \pm 20\text{ V}$	I_{GSS}			±10	μA

ON CHARACTERISTICS (Note 5)

Static Drain-to-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 1.0\text{ A}$	$R_{DS(on)}$		4.0	4.8	Ω
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 50\text{ μA}$	$V_{GS(th)}$	3.0		4.5	V
Forward Transconductance	$V_{DS} = 15\text{ V}, I_D = 1.2\text{ A}$	g_{FS}		1.7		S

DYNAMIC CHARACTERISTICS

Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	C_{iss}		274		pF
Output Capacitance		C_{oss}		34		
Reverse Transfer Capacitance		C_{rss}		7.0		
Total Gate Charge	$V_{DD} = 300\text{ V}, I_D = 2.4\text{ A},$ $V_{GS} = 10\text{ V}$	Q_g		10.1		nC
Gate-to-Source Charge		Q_{gs}		2.4		
Gate-to-Drain ("Miller") Charge		Q_{gd}		5.3		
Plateau Voltage	$V_{DD} = 300\text{ V}, I_D = 2.4\text{ A}, V_{OS} = 10\text{ V}$	V_{GP}		6.4		V
Gate Resistance		R_g		4.9		Ω

RESISTIVE SWITCHING CHARACTERISTICS

Turn-On Delay Time	$V_{DD} = 300\text{ V}, I_D = 2.4\text{ A},$ $V_{GS} = 10\text{ V}, R_G = 5\text{ Ω}$	$t_{d(on)}$		9.0		ns
Rise Time		t_r		7.0		
Turn-Off Delay Time		$t_{d(off)}$		15		
Fall Time		t_f		7.0		

SOURCE-DRAIN DIODE CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Diode Forward Voltage	$I_S = 2.4\text{ A}, V_{GS} = 0\text{ V}$	V_{SD}			1.6	V
Reverse Recovery Time	$V_{GS} = 0\text{ V}, V_{DD} = 30\text{ V}$ $I_S = 2.4\text{ A}, di/dt = 100\text{ A/μs}$	t_{rr}		240		ns
Reverse Recovery Charge		Q_{rr}		0.7		μC

5. Pulse Width ≤ 380 μs, Duty Cycle ≤ 2%.

TYPICAL CHARACTERISTICS

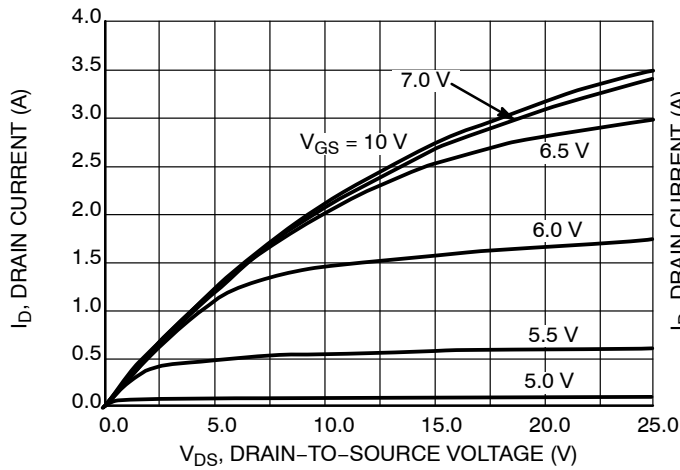


Figure 1. On-Region Characteristics

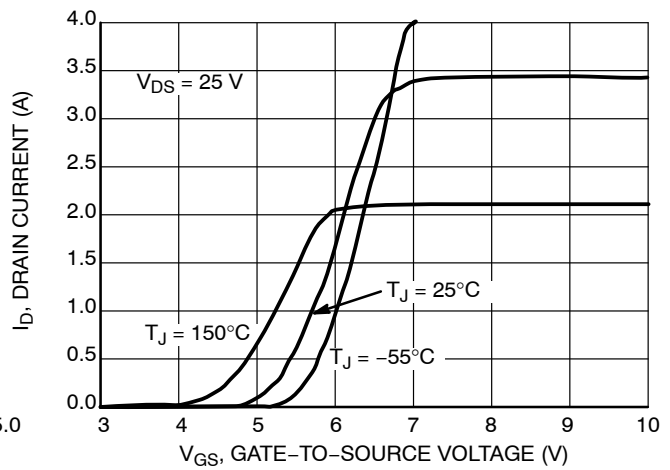


Figure 2. Transfer Characteristics

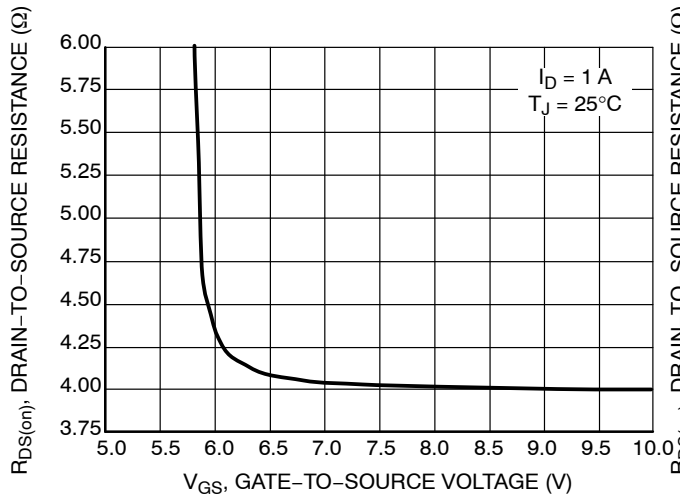


Figure 3. On-Region versus Gate-to-Source Voltage

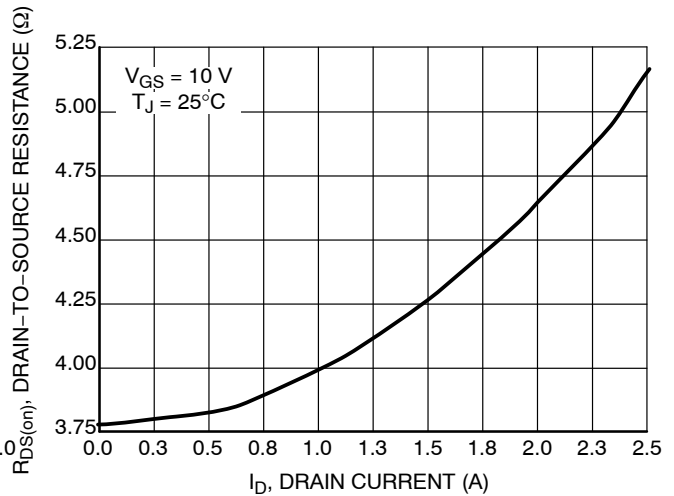


Figure 4. On-Resistance versus Drain Current and Gate Voltage

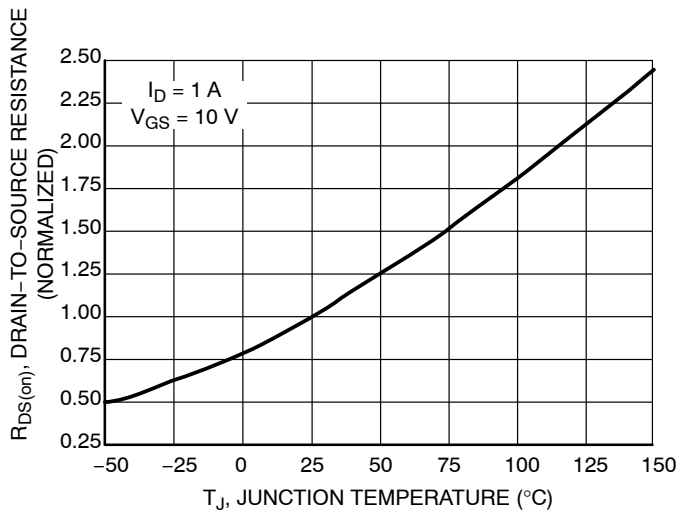


Figure 5. On-Resistance Variation with Temperature

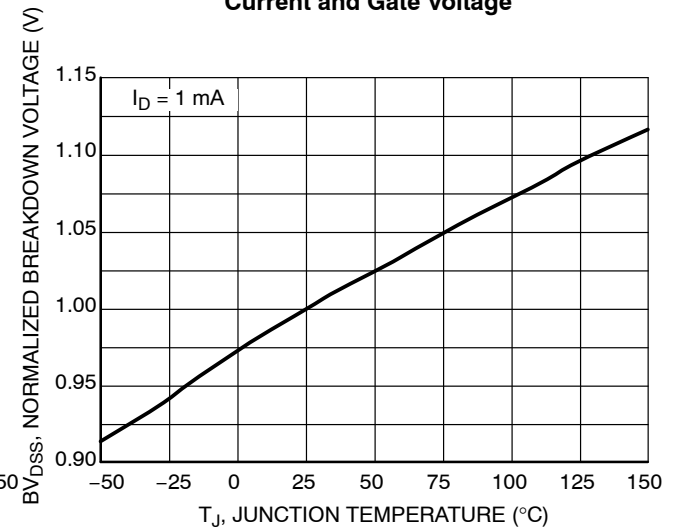


Figure 6. BV_{DSS} Variation with Temperature

TYPICAL CHARACTERISTICS

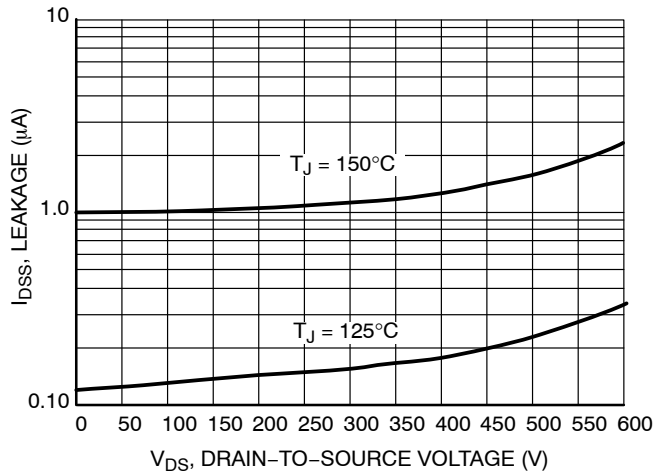


Figure 7. Drain-to-Source Leakage Current versus Voltage

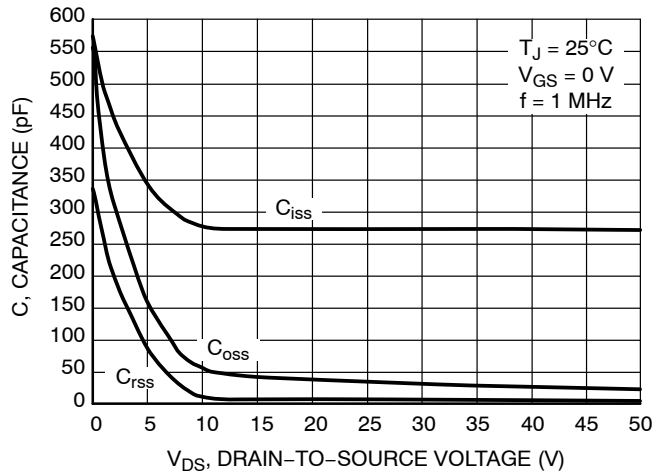


Figure 8. Capacitance Variation

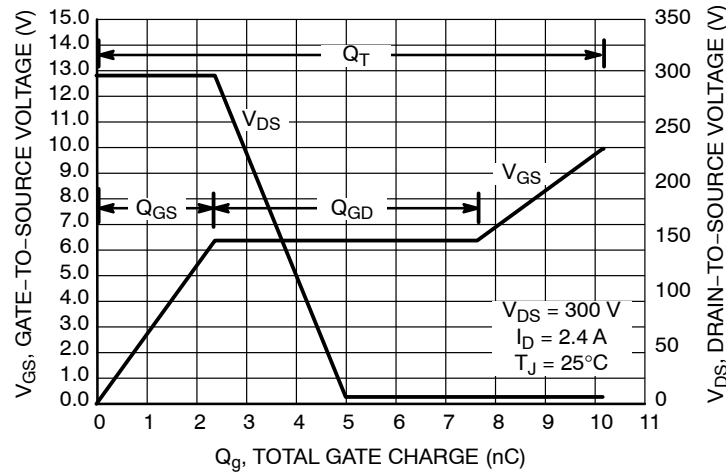


Figure 9. Gate-to-Source Voltage and Drain-to-Source Voltage versus Total Charge

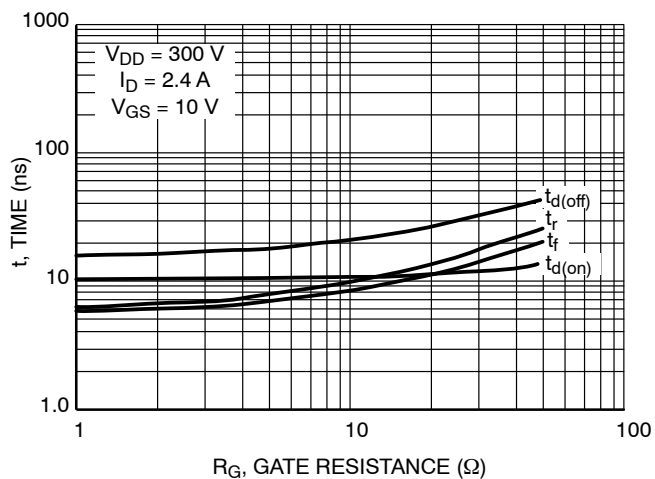


Figure 10. Resistive Switching Time Variation versus Gate Resistance

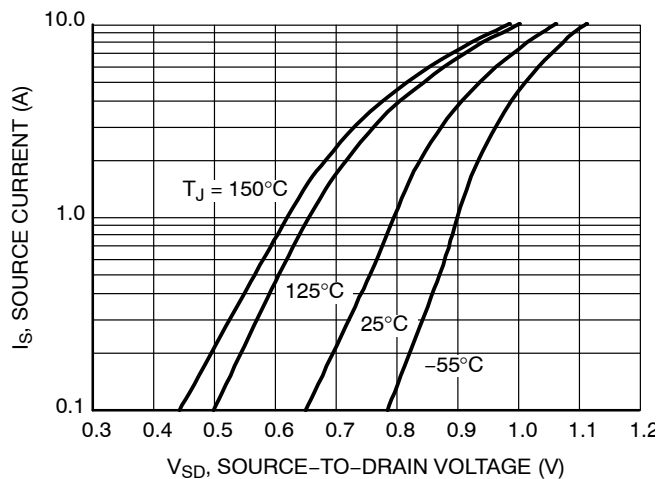
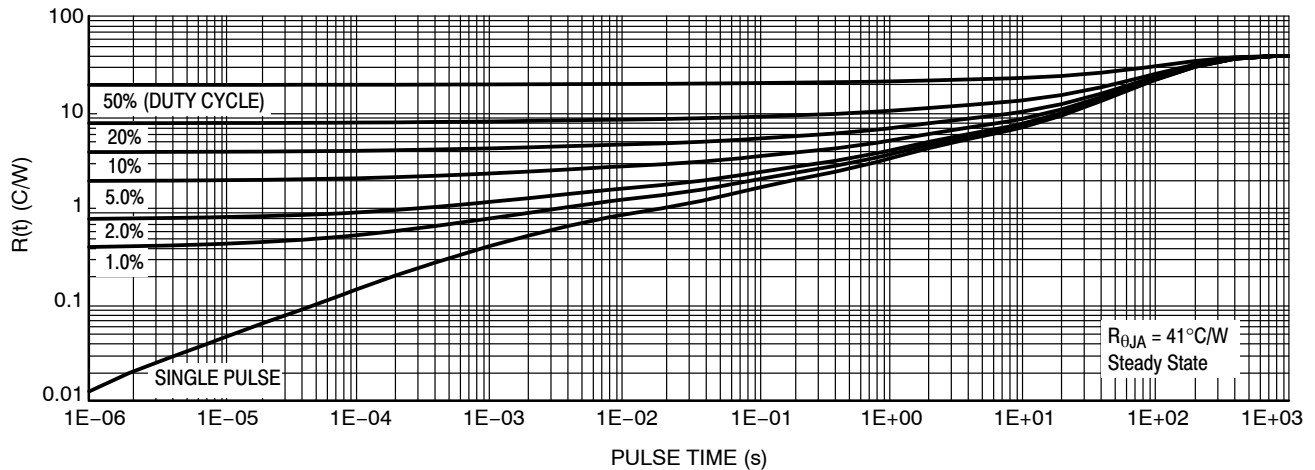
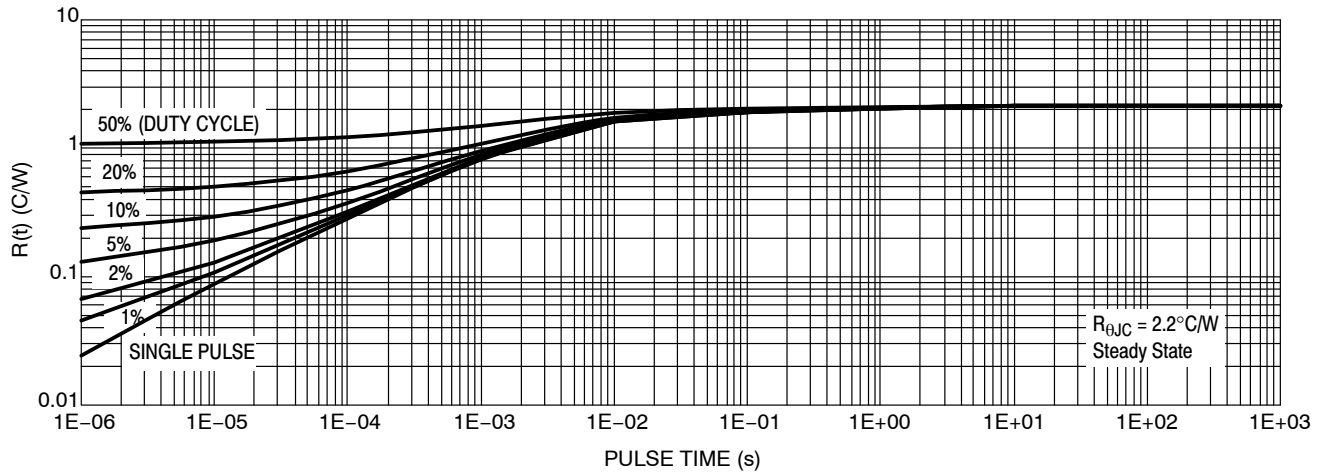
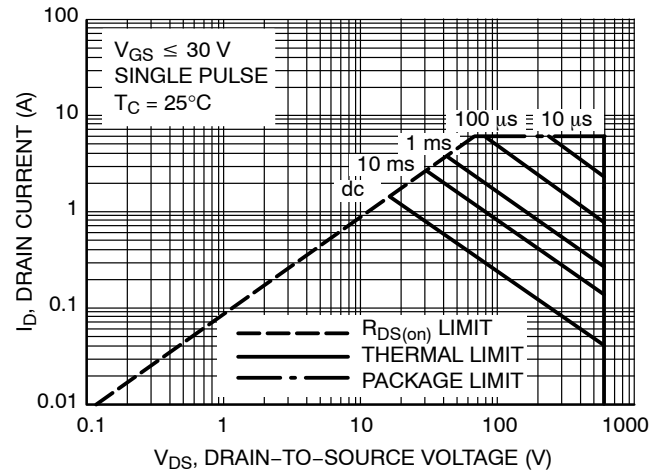
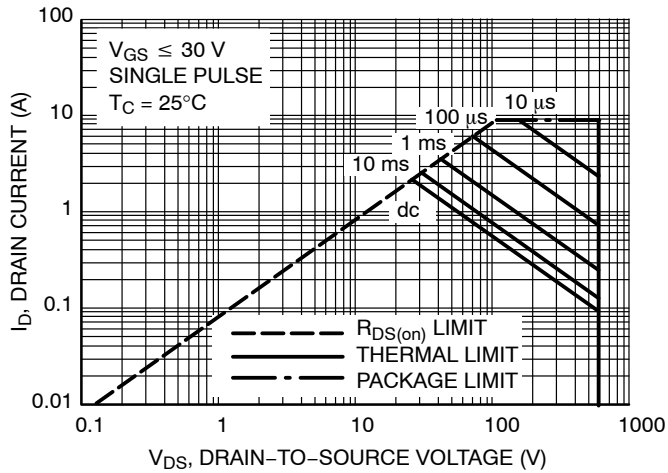


Figure 11. Diode Forward Voltage versus Current

TYPICAL CHARACTERISTICS



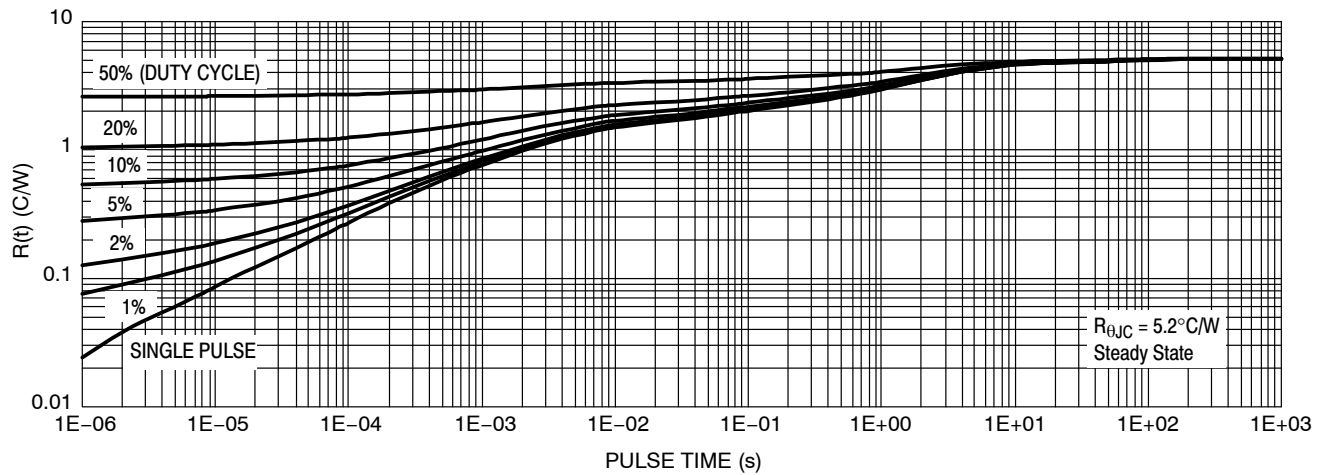


Figure 16. Thermal Impedance (Junction-to-Case) for NDF02N60Z

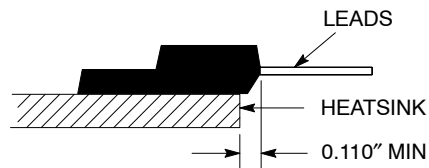


Figure 17. Isolation Test Diagram

Measurement made between leads and heatsink with all leads shorted together.

*For additional mounting information, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NDF02N60Z, NDP02N60Z, NDD02N60Z

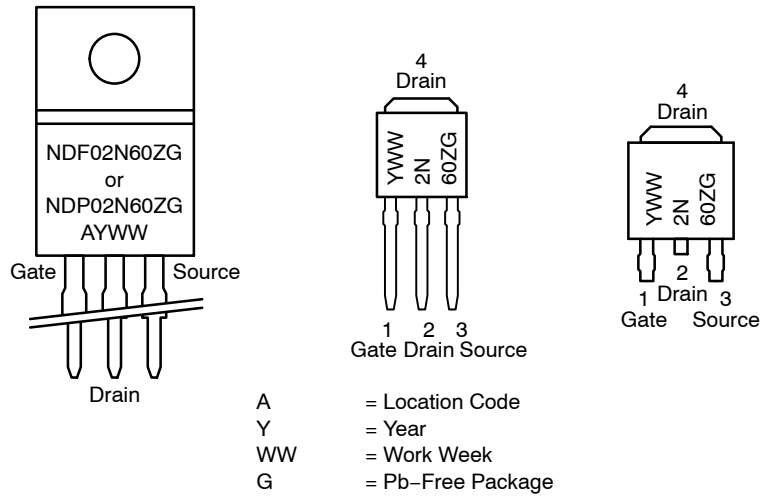
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ORDERING INFORMATION

Order Number	Package	Shipping [†]
NDF02N60ZG	TO-220FP (Pb-Free)	50 Units / Rail
NDP02N60ZG	TO-220AB (Pb-Free)	50 Units / Rail In Development
NDD02N60Z-1G	IPAK (Pb-Free)	75 Units / Rail
NDD02N60ZT4G	DPAK (Pb-Free)	2500 / Tape & Reel

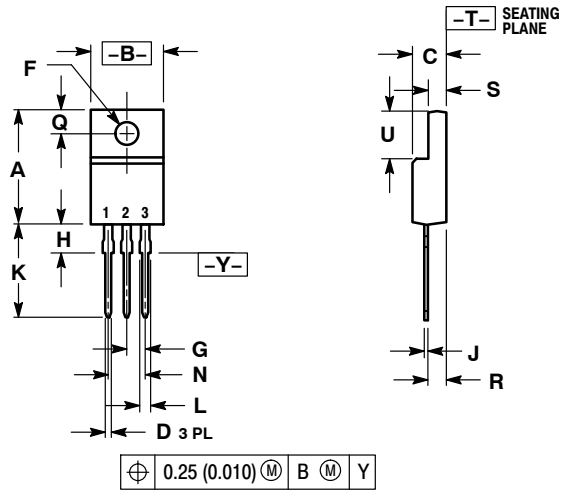
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MARKING DIAGRAMS



PACKAGE DIMENSIONS

TO-220 FULLPAK
CASE 221D-03
ISSUE J

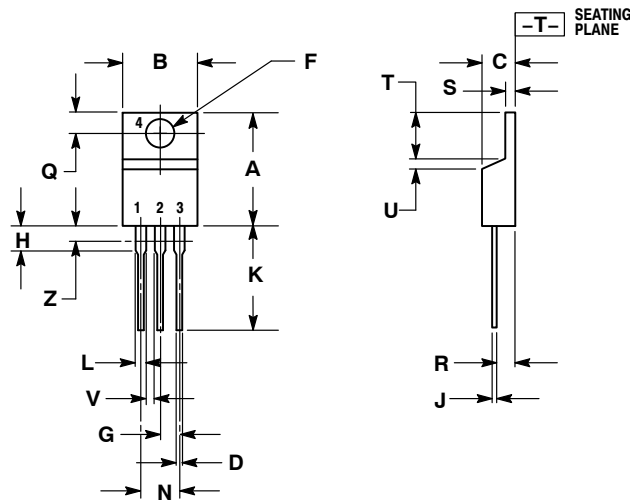


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH
 3. 221D-01 THRU 221D-02 OBSOLETE, NEW STANDARD 221D-03.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.617	0.635	15.67	16.12
B	0.392	0.419	9.96	10.63
C	0.177	0.193	4.50	4.90
D	0.024	0.039	0.60	1.00
F	0.116	0.129	2.95	3.28
G	0.100 BSC		2.54 BSC	
H	0.118	0.135	3.00	3.43
J	0.018	0.025	0.45	0.63
K	0.503	0.541	12.78	13.73
L	0.048	0.058	1.23	1.47
N	0.200 BSC		5.08 BSC	
Q	0.122	0.138	3.10	3.50
R	0.099	0.117	2.51	2.96
S	0.092	0.113	2.34	2.87
U	0.239	0.271	6.06	6.88

- STYLE 1:
- PIN 1. GATE
 - DRAIN
 - SOURCE

TO-220AB
CASE 221A-09
ISSUE AE



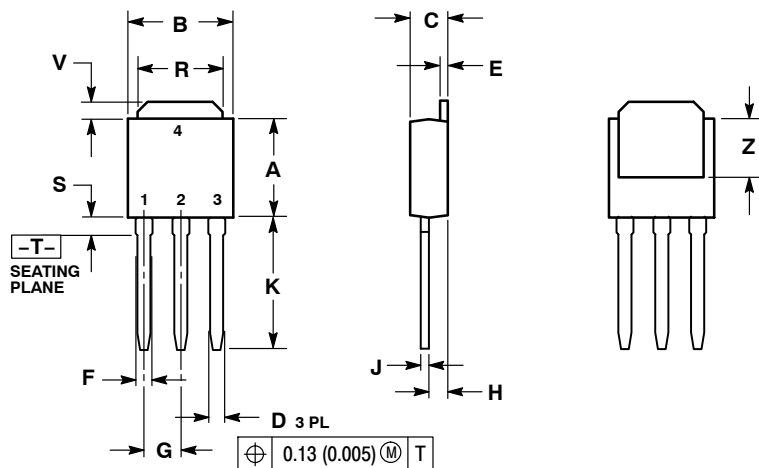
- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

- STYLE 5:
- PIN 1. GATE
 - DRAIN
 - SOURCE
 - DRAIN

PACKAGE DIMENSIONS

IPAK
CASE 369D-01
ISSUE B

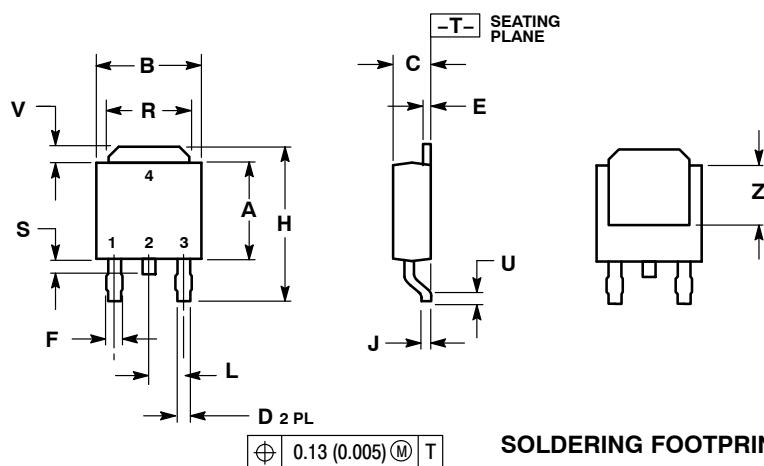


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090 BSC	2.29 BSC		
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

- STYLE 2:
- PIN 1: GATE
2: DRAIN
3: SOURCE
4: DRAIN

DPAK
CASE 369AA-01
ISSUE A

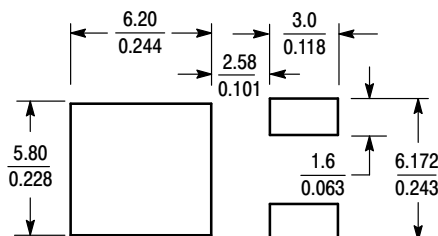


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.22
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.025	0.035	0.63	0.89
E	0.018	0.024	0.46	0.61
F	0.030	0.045	0.77	1.14
H	0.386	0.410	9.80	10.40
J	0.018	0.023	0.46	0.58
L	0.090 BSC	2.29 BSC		
R	0.180	0.215	4.57	5.45
S	0.024	0.040	0.60	1.01
U	0.020	---	0.51	---
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

- STYLE 2:
- PIN 1: GATE
2: DRAIN
3: SOURCE
4: DRAIN

SOLDERING FOOTPRINT*



SCALE 3:1 (mm/inches)

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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